

An object of the present invention resides in a semiconductor device in which flip chip bonding can be performed without any underfill.

The method of the present invention includes the steps of: forming an electrically insulating layer on a region, which is on a wafer having a plurality of semiconductor devices formed thereon and which contains a part of a first semiconductor device and a part of a second semiconductor device, so that the electrically insulating layer is formed to extend over the first and second semiconductor devices; forming an external connection terminal on the electrically insulating layer; removing the electrically insulating layer in a region between the first and second semiconductor devices; and dicing the wafer in the region in which the electrically insulating layer is removed.